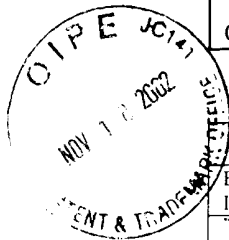


First Named Inventor	Wang Zhongze	<p align="center">INFORMATION DISCLOSURE STATEMENT FORM PTO-1449</p>
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	Country	No.			

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Examiner Signature	<i>Michael Frank</i>	Date Considered	6/2/03
<p>*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>			